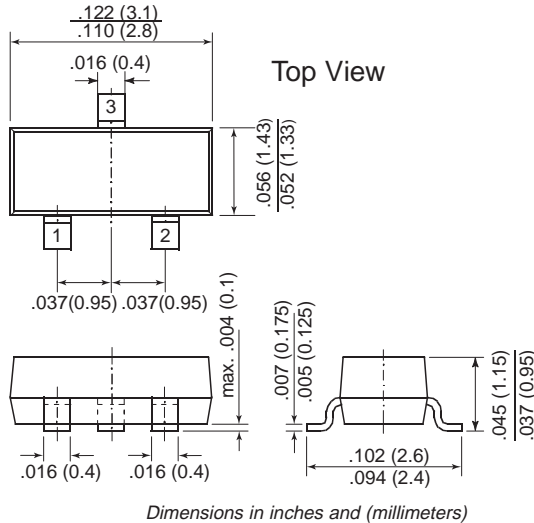


## Small Signal Transistors (NPN)



**New Product**

### SOT-23



### Features

- NPN Silicon Epitaxial Planar Transistor for switching and amplifier applications.
- As complementary type, the PNP transistor MMBTA56 is recommended.
- This transistor is also available in the TO-92 case with the type designation MPSA06.

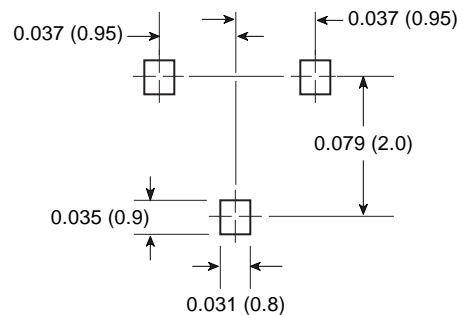
### Mechanical Data

**Case:** SOT-23 Plastic Package

**Weight:** approx. 0.008g

**Marking Code:** 1GM

### Mounting Pad Layout SOT-23



### Maximum Ratings and Thermal Characteristics (T<sub>A</sub> = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V <sub>CBO</sub>	80	V
Collector-Emitter Voltage	V <sub>CEO</sub>	80	V
Emitter-Base Voltage	V <sub>EBO</sub>	4.0	V
Collector Current	I <sub>C</sub>	500	mA
Power Dissipation at T <sub>SB</sub> = 50 °C	P <sub>tot</sub>	255 <sup>1)</sup> 300 <sup>2)</sup>	mW
Thermal Resistance Junction to Ambient Air	R <sub>θJA</sub>	560 <sup>1)</sup>	°C/W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature Range	T <sub>s</sub>	-65 to +150	°C

**Note:** (1) Device on fiberglass substrate, see layout on third page.  
 (2) Device on alumina substrate.

**Small Signal Transistors (NPN)**

**Electrical Characteristics** ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1 \text{ mA}, I_B = 0$	80	—	—	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 100 \mu\text{A}, I_C = 0$	4.0	—	—	V
Collector-Emitter Cutoff Current	$I_{CES}$	$V_{CE} = 60 \text{ V}, I_B = 0$	—	—	100	nA
Collector-Base Cutoff Current	$I_{CBO}$	$V_{CB} = 80 \text{ V}, I_E = 0$	—	—	100	nA
Collector Saturation Voltage	$V_{CEsat}$	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$	—	—	0.25	V
Base-Emitter On Voltage	$V_{BE(on)}$	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$	—	—	1.2	V
DC Current Gain	$h_{FE}$	$V_{CE} = 1 \text{ V}, I_C = 10 \text{ mA}$ $V_{CE} = 1 \text{ V}, I_C = 100 \text{ mA}$	100 100	— —	— —	— —
Gain-Bandwidth Product	$f_T$	$V_{CE} = 2 \text{ V}, I_C = 10 \text{ mA}$ $f = 100 \text{ MHz}$	100	—	—	MHz

**Note:**

(1) Device on fiberglass substrate, see layout on next page

**Layout for  $R_{\theta JA}$  test**

Thickness: Fiberglass 0.059 in. (1.5 mm)  
Copper leads 0.012 in. (0.3 mm)

